

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
a cobalt including layer having oxidation resistive and
fluorinated acid resistive; and
5 a clad layer for cladding said cobalt including layer.

2. The semiconductor device as cited in Claim 1, wherein
said cobalt including layer comprising of the cobalt tungsten
phosphor layer.

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3. The semiconductor device as cited in Claim 1, wherein
said clad layer comprising of a cobalt silicide layer.

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4. The semiconductor device as cited in Claim 1, wherein
said cobalt including layer being formed on a copper wiring
face.

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5. A method for manufacturing a semiconductor device
comprising the steps of:
forming a cobalt including layer; and
forming a cobalt silicide layer on said surface of the cobalt
including layer.

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6. The method as cited in claim 5, wherein
said cobalt silicide layer being formed by exposing said cobalt
including layer in a silane system gas.

7. The method as cited in claim 5, wherein
said cobalt including layer is a cobalt tungsten phosphor layer.